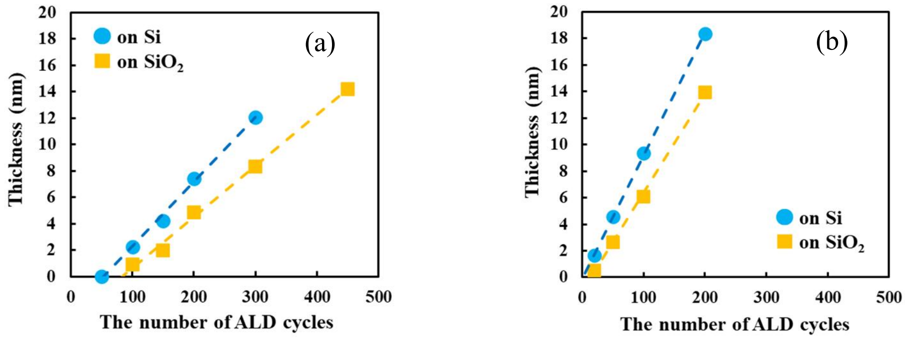

Fig. 1. Dependence of the SiN film thickness on the number of ALD cycles using (a) NH_3 and (b) N_2H_4.

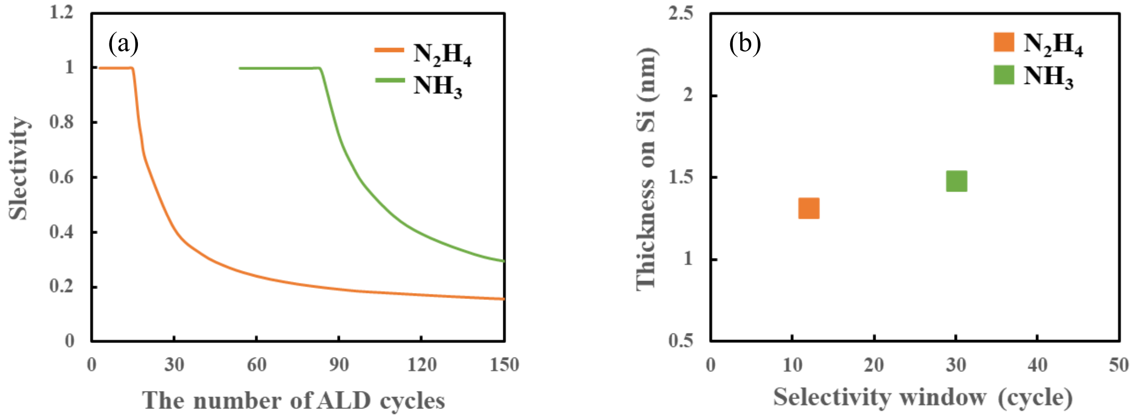

Fig. 2. Evaluation of SiN ALD using NH_3 and N_2H_4. (a) Selectivity calculated from the SiN film thicknesses on the growth area (Si) and nongrowth area (SiO_2). (b) SiN film thickness accumulated on the growth area (Si) before SiN growth initiates on the nongrowth area (SiO_2).

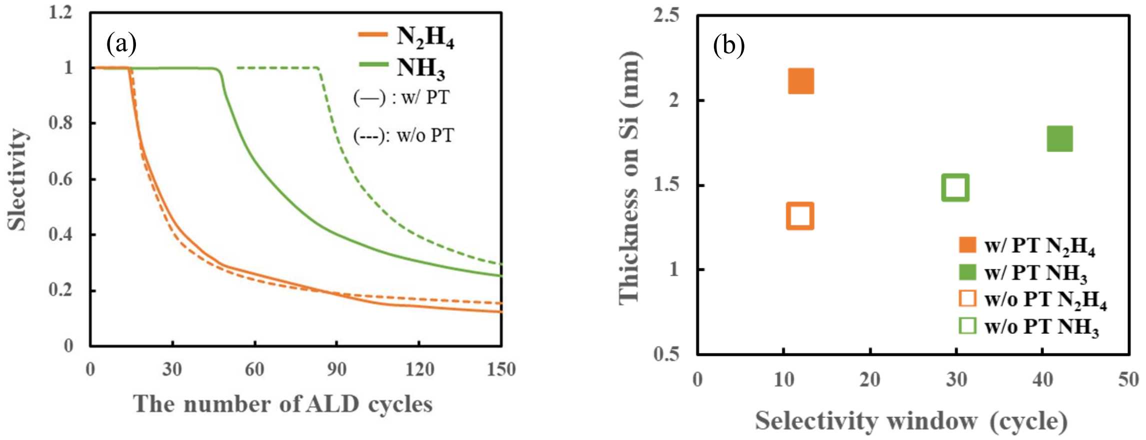

Fig. 3. Evaluation of SiN ALD with N_2H_4 pretreatment (PT). (a) Selectivity calculated from the SiN film thicknesses on the growth area (Si) and nongrowth area (SiO_2). (b) SiN film thickness accumulated on growth area (Si) before SiN growth initiates on nongrowth area (SiO_2).